

HAF2015RJ

Silicon N Channel MOS FET Series Power Switching

REJ03G1141-0300 Rev.3.00 Aug 27, 2007

Description

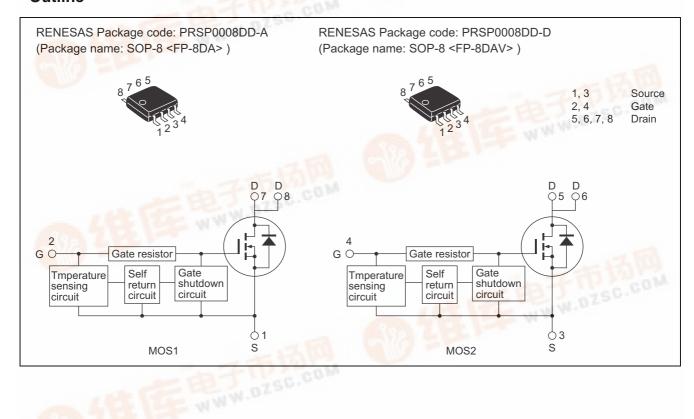
This FET has the over temperature shut-down capability sensing to the junction temperature.

This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc.

Features

- Logic level operation (5 to 6 V Gate drive)
- High endurance capability against to the short circuit
- Built-in the over temperature shut-down circuit
- Temperature hysteresis type.
- High density mounting.

Outline





Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V_{GSS}	16	V
	V _{GSS}	-2.5	V
Drain current	I _D	2	A
Drain peak current	I _{D (pulse)} Note 1	4	A
Body-drain diode reverse drain current	I _{DR}	2	A
Avalanche current	I _{AP} Note 4	0.54	A
Avalanche energy	E _{AR} Note 4	25	mJ
Channel dissipation	Pch Note 2	2	W
Channel dissipation	Pch Note 3	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \mu s$, duty cycle $\le 1\%$

- 2. 1 Drive operation: When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW \leq 10 s
- 3. 2 Drive operation: When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW ≤ 10 s
- 4. Tch = 25°C, Rg > 50 Ω

Typical Operation Characteristics

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	V _{IH}	3.5	_	_	V	
	V _{IL}	_	_	1.2	V	
Input current	I _{IH1}	_	_	100	μΑ	Vi = 5 V, V _{DS} = 0
(Gate non shut down)	I _{IH2}	_	_	50	μΑ	Vi = 3.5 V, V _{DS} = 0
	I _{IL}	_	_	1	μΑ	Vi = 1.2 V, V _{DS} = 0
Input current	I _{IH} (sd) 1	_	0.53	_	mA	Vi = 8 V, V _{DS} = 0
(Gate shut down)	I _{IH} (sd) 2	_	0.2	_	mA	Vi = 3.5 V, V _{DS} = 0
Shut down temperature	Tsd	_	175	_	°C	Channel temperature
Hysteresis temperature	Thr	_	120	_	°C	Channel temperature
Gate operation voltage	V _{OP}	3.5	_	12	V	

Electrical Characteristics

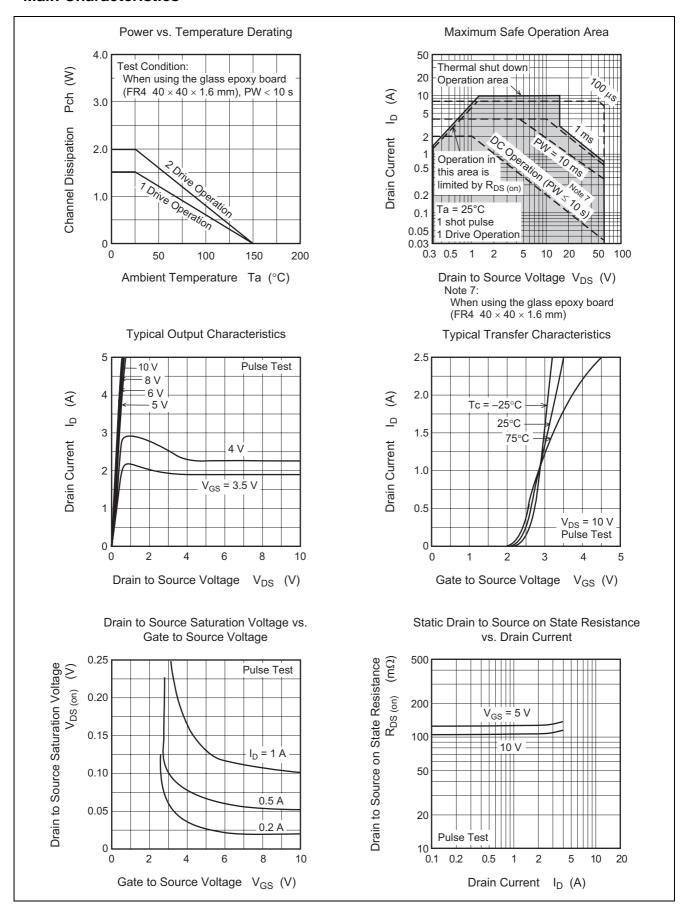
 $(Ta = 25^{\circ}C)$

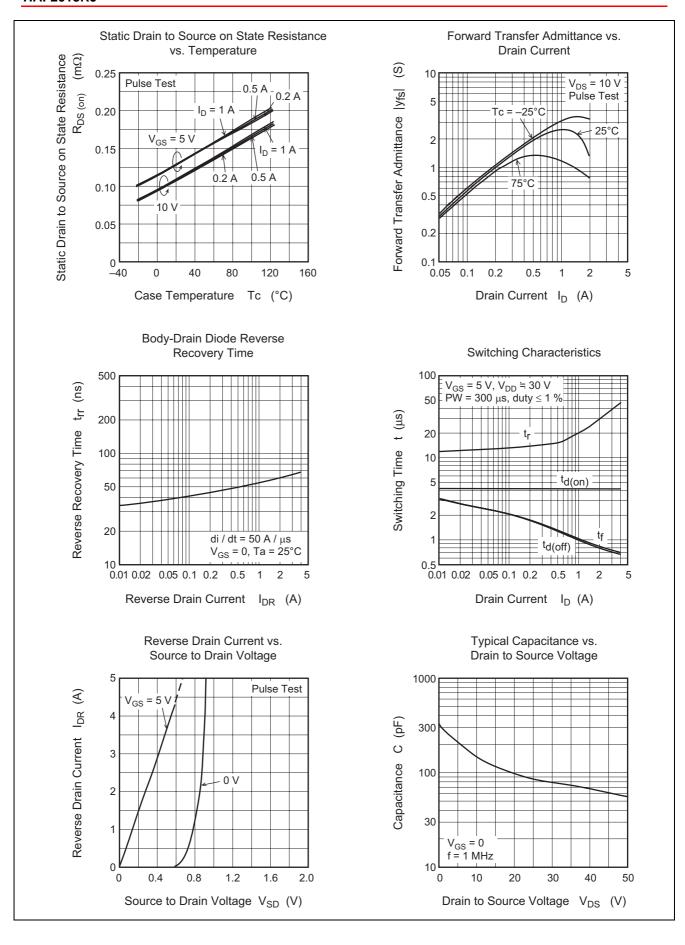
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain current	I _{D1}	0.7	_	_	Α	$V_{GS} = 3.5 \text{ V}, V_{DS} = 2 \text{ V}$
	I_{D2}	_	_	10	mA	$V_{GS} = 1.2 \text{ V}, V_{DS} = 2 \text{ V}$
Drain to source breakdown voltage	V _{(BR) DSS}	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	V _{(BR) GSS}	16	_	_	V	$I_G = 500 \mu\text{A}, V_{DS} = 0$
	$V_{(BR) GSS}$	-2.5			V	$I_G = -100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I _{GSS1}	_		100	μΑ	$V_{GS} = 5 \text{ V}, V_{DS} = 0$
	I _{GSS2}	_	_	50	μΑ	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
	I _{GSS3}	_	_	1	μΑ	$V_{GS} = 1.2 \text{ V}, V_{DS} = 0$
	I _{GSS4}	_	_	-100	μΑ	$V_{GS} = -2.4 \text{ V}, V_{DS} = 0$
Input current (shut down)	I _{GS (op) 1}	_	0.53	_	mA	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	I _{GS (op) 2}	_	0.2	_	mA	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS1}	_	_	10	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0$
	I _{DSS2}	_	_	10	μΑ	$V_{DS} = 48 \text{ V}, V_{GS} = 0$
						Ta = 125°C
Gate to source cutoff voltage	V _{GS (off)}	1.4	_	2.5	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	R _{DS (on)}	_	130	200	mΩ	$I_D = 1 \text{ A}, V_{GS} = 5 \text{ V}^{\text{Note 5}}$
	R _{DS (on)}	_	110	160	mΩ	$I_D = 1 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 5}}$
Forward transfer admittance	y _{fs}	0.5	2.5		S	$I_D = 1 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note 5}}$
Output capacitance	Coss	_	139		pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0$
						f = 1 MHz
Turn-on delay time	t _{d (on)}	_	4.2		μs	I _D = 1 A
Rise time	t _r	_	20		μs	$V_{GS} = 5 V$
Turn-off delay time	t _{d (off)}	_	1		μs	$R_L = 30 \Omega$
Fall time	t _f		1		μs	
Body-drain diode forward voltage	V_{DF}	_	0.82		V	$I_F = 2 A, V_{GS} = 0$
Body-drain diode reverse recovery time	t _{rr}	_	55	_	ns	$I_F = 2 A, V_{GS} = 0$
						$di_F/dt = 50 A/\mu s$
Over load shut down operation time Note6	t _{os1}	_	15	_	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 16 \text{ V}$

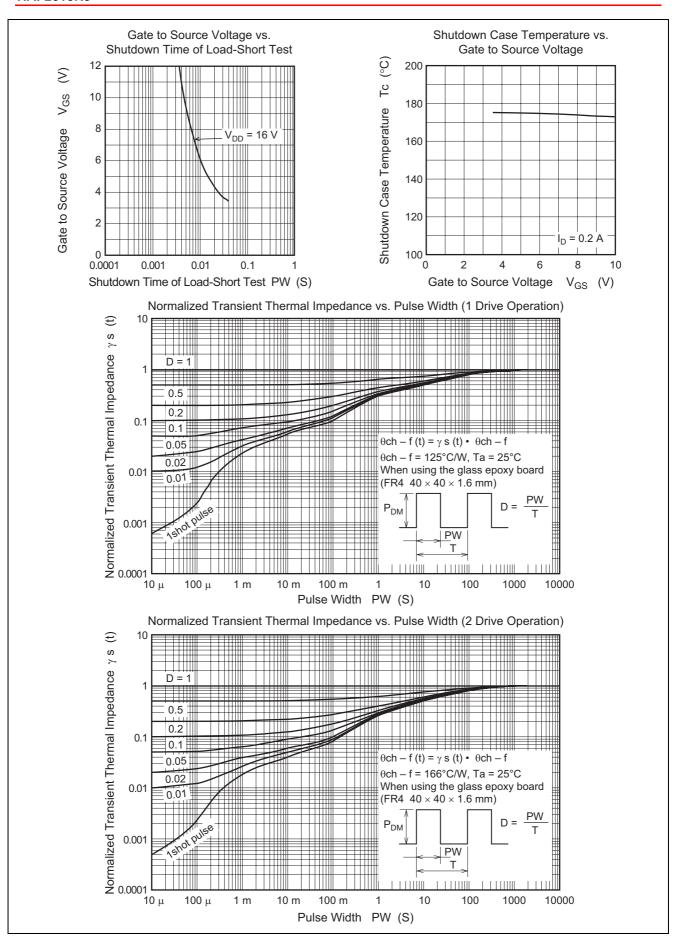
Notes: 5. Pulse test

6. Including the junction temperature rise of the over loaded condition.

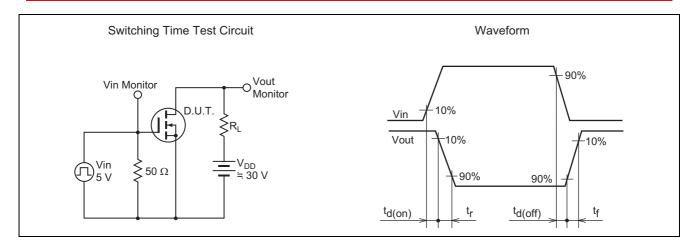
Main Characteristics



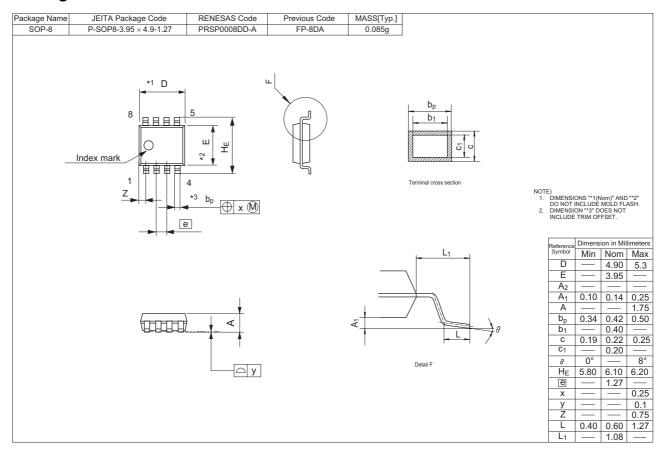


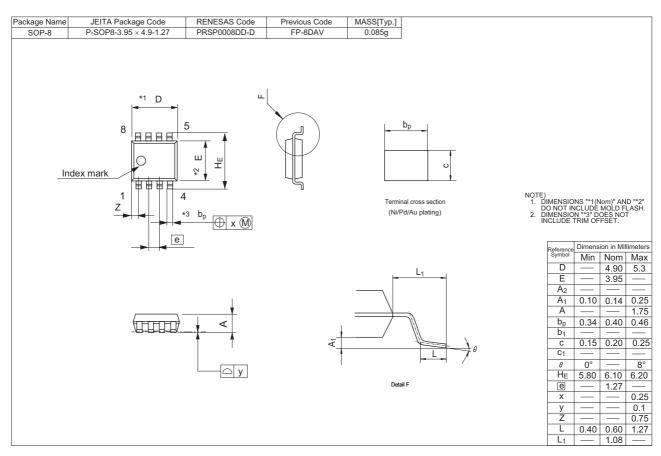


HAF2015RJ



Package Dimensions





HAF2015RJ

Ordering Information

Part No.	Quantity	Shipping Container
HAF2015RJ-EL	2500 pcs/Reel	Embossed tape

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